



CHENMKO ENTERPRISE CO.,LTD

Halogens free devices

**SURFACE MOUNT
PNP SILICON Transistor**

VOLTAGE 150 Volts CURRENT 0.2 Ampere

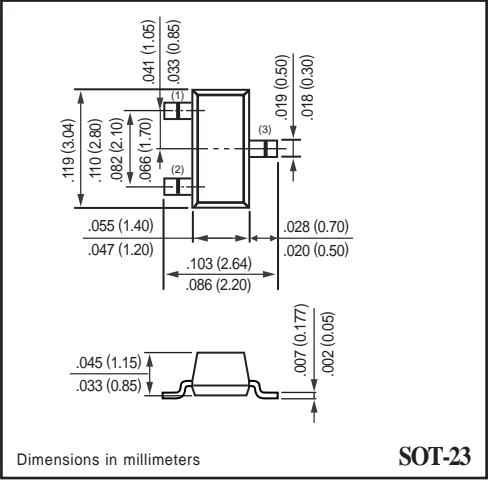
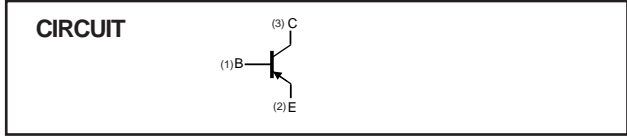
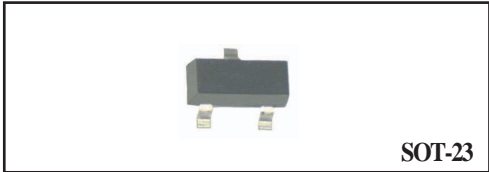
CHT5401GP

APPLICATION
 * Telephony and professional communication equipment.
 * Other switching applications.

FEATURE
 * Small flat package. (SOT-23)
 * Suitable for high packing density.

CONSTRUCTION
 * PNP transistors in one package.

MARKING
 * VT



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CB0}	collector-base voltage	open emitter	-	-160	V
V _{CEO}	collector-emitter voltage	open base	-	-150	V
V _{EBO}	emitter-base voltage	open collector	-	-5.0	V
I _c	collector current (DC)		-	-200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	-	225	mW
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		-	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

RATING CHARACTERISTIC CURVES (CHT5401GP)

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	420	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	$V_{CB} = -120\text{ V}$	–	-50	nA
I_{EBO}	emitter cut-off current	$V_{EB} = 3.0\text{ V}$	–	-50	nA
h_{FE}	DC current gain	$I_C = -1.0\text{ mA}; V_{CE} = -5\text{ V}$ $I_C = -10\text{ mA}; V_{CE} = -5\text{ V}$ $I_C = -50\text{ mA}; V_{CE} = -5\text{ V}$	50 60 50	– 240 –	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -1.0\text{ mA}$	–	-0.2	V
		$I_C = -50\text{ mA}; I_B = -5.0\text{ mA}$	–	-0.5	V
V_{BEsat}	base-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -1.0\text{ mA}$	–	-1.0	V
		$I_C = -50\text{ mA}; I_B = -5.0\text{ mA}$	–	-1.0	V
C_{ob}	collector capacitance	$I_E = I_e = 0; V_{CB} = -10\text{ V}; f = 1\text{ MHz}$	–	6.0	pF
h_{fe}		$V_{CE} = -10\text{ V}, I_C = -1.0\text{ mA}, f = 1.0\text{ KHz}$	40	200	
f_T	transition frequency	$I_C = -50\text{ mA}; V_{CE} = 10\text{ V}; f = 100\text{ MHz}$	100	300	MHz
F	noise figure	$I_C = 200\text{ }\mu\text{A}; V_{CE} = 5\text{ V}; R_S = 10\text{ }\Omega; f = 10\text{ Hz to }15.7\text{ KHz}$	–	8.0	dB